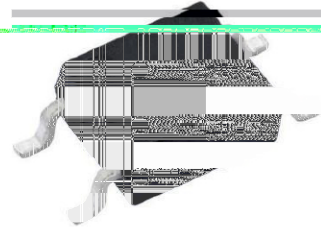


1. Features

- Current transfer ratio(CTR : MIN. 50% at $I_E = 5mA, V_{CE} = 5V, T_a=25^{\circ}C$)
- High input -output isolation voltage ($V_{ISO}=3,750Vrms$)
- High collector-emitter voltage ($V_{CEO} = 80V$)
- SOP-4 package
- 55 °C to 110 °C



b. (1) (2) (3) (4) (5) (6) (7) (8) (9) (10) (11) (12) (13) (14) (15) (16) (17) (18) (19) (20) (21) (22) (23) (24) (25) (26) (27) (28) (29) (30) (31) (32) (33) (34) (35) (36) (37) (38) (39) (40) (41) (42) (43) (44) (45) (46) (47) (48) (49) (50) (51) (52) (53) (54) (55) (56) (57) (58) (59) (60) (61) (62) (63) (64) (65) (66) (67) (68) (69) (70) (71) (72) (73) (74) (75) (76) (77) (78) (79) (80) (81) (82) (83) (84) (85) (86) (87) (88) (89) (90) (91) (92) (93) (94) (95) (96) (97) (98) (99) (100)

2. Instructions

- The OR-357 series device consists of an infrared led, photo transistor detector.
 - (1) low level manufacturing
 - (2) Pin pitch of OR-357 is 2.54mm
 - (3) The product is sensitive to heat and requires non-densification.

- Programmable controllers
- SYSTEM ADDRESS, measuring instruments

4. Basic electrical parameters (continued)

Symbol	Parameter	Unit	Value	Test Conditions
I_E	Emitter Current	mA	5	
T_a	Temperature	°C	25	
V_{CE}	Collector-Emitter Voltage	V	5	
P_C	Collector Power	mW	150	
V_{CE0}	Collector-Emitter Voltage (Open)	V	80	
P_C	Consume Power	mW	150	
V_{CE0}	Collector-Emitter Voltage	V	80	
V_{CE0}	Collector-Emitter Voltage	V	80	
T_a	Temperature	°C	25	

